Central™
Semiconductor Corp.

PROCESS CP215

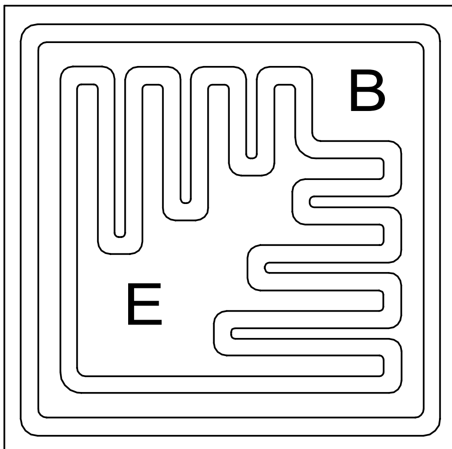
Small Signal Transistors

NPN - Saturated Switch Transistor Chip

PROCESS DETAILS

PROCESS	EPITAXIAL PLANAR
DIE SIZE	21 x 21 MILS
DIE THICKNESS	9.0 MILS
BASE BONDING PAD AREA	4.3 x 4.3 MILS
EMITTER BONDING PAD AREA	5.0 x 5.0 MILS
TOP SIDE METALIZATION	Al - 15,000Å
BACK SIDE METALIZATION	Au - 10,000Å

GEOMETRY



BACKSIDE COLLECTOR

PRINCIPAL DEVICE TYPES

2N3725
2N3725A
MPQ3725
MPQ3725A

**Please refer to
selection guide on page 18.**

145 Adams Avenue
Hauppauge, NY 11788 USA
Phone (631) 435-1110
Fax (631) 435-1824
www.centralsemi.com